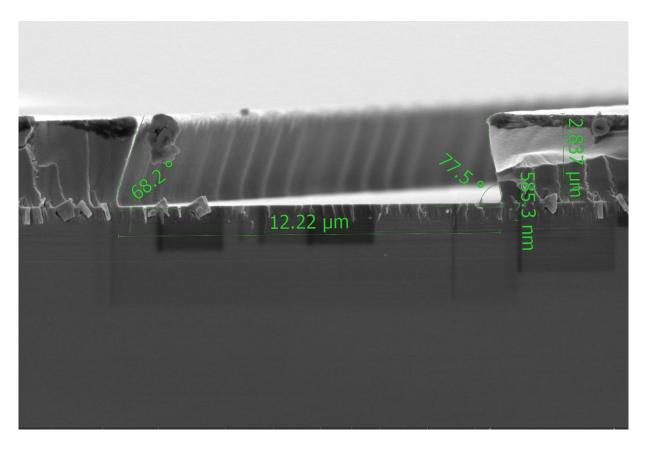
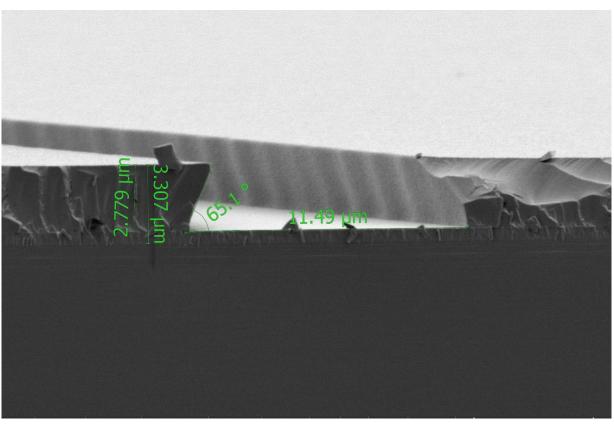
Characterization of AZ1529 Image Reversal Photoresist Profiles Oct. 30, 2025 By MDM

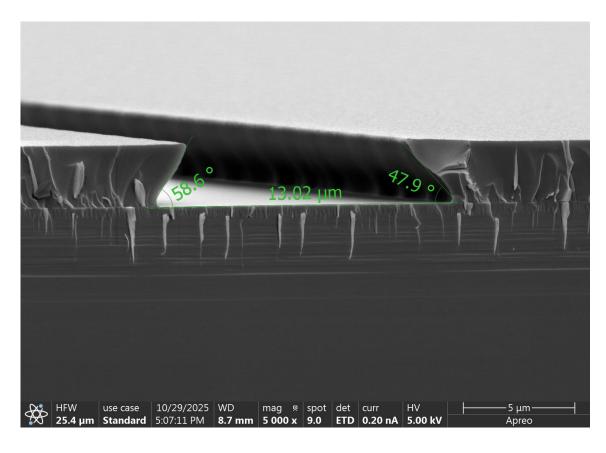
- Goal: To achieve significant undercut for lift-off
- Conditions: 12.1 mW/cm² at 436 nm
- Using an MA-6 Suss Mask Aligner
- All soft bakes at 115°C for 1.5 min, on a hot plate
- No hard bake
- 40 Sec Flood Exposure followed by Image Reversal in a Yes oven.
- Develop 1 min in AZ 300 developer

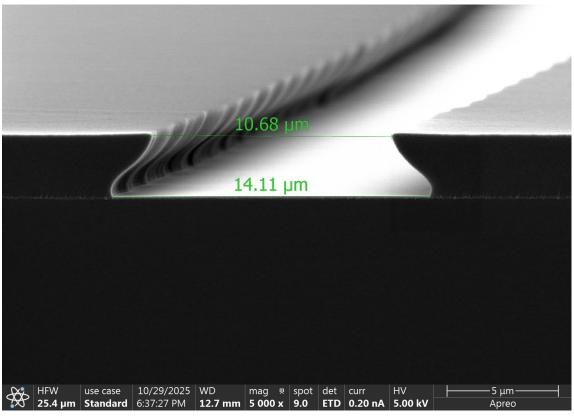
17 second Exposure, Oxidized silicon wafer





20 second Exposure, Oxidized silicon wafer and metal coated wafer





Oxidized Wafer

Metal Coated Wafer: this was a scrap wafer so not entirely sure what metal was on there

23 second Exposure, Metal coated wafer

